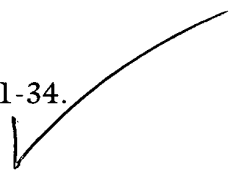


Cancel claims 1-34.



35. (Amended) A method of fabricating a flip chip semiconductor die,
comprising depositing a solder material on each of a plurality of connection sites, wherein
the diameter of each said deposited solder material is about 10 microns or less.

A1

44. (New) The method of claim 35, wherein a pitch between respective ones of
said deposited solder material is less than about 100 microns.

A2

45. (New) The method of claim 44, wherein a pitch between respective ones of
said deposited solder material is less than about 25 microns.
